

Serbian Ceramic Society Conference ADVANCED CERAMICS AND APPLICATION X New Frontiers in Multifunctional Material Science and Processing

Serbian Ceramic Society Institute of Technical Sciences of SASA Institute for Testing of Materials Institute of Chemistry Technology and Metallurgy Institute for Technology of Nuclear and Other Raw Mineral Materials

PROGRAM AND THE BOOK OF ABSTRACTS

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In this contribution, the adsorption of organophosphate pesticide dimethoate on two commercially available graphene-oxides has been investigated. The materials were characterized by different physico-chemical methods. Careful structural characterization of adsorbents was combined with batch adsorption experiments. It was shown that 1 g of both graphene-oxides is capable of adsorbing 9×10^{-3} mol dm⁻³ of dimethoate at 25 °C. A satisfactory agreement of both sets of experimental results with the Langmuir isotherm model suggests the monolayer adsorption on the homogenous surface. The adsorption was also investigated at 30 and 35 °C. The results showed that the concentration of adsorbed dimethoate increases with temperature for both studied adsorbents. Investigated graphene-oxides were successfully used for the removal of dimethoate from water.

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Correlation of the total induced amorphization in SiC crystal with the ion implantation fluence

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During the ion implantation process, regardless if it was attentional or not, amorphization will be introduced into the crystal structure. Depending on the chosen ions, different quantities of the amorphization will be introduced for the same applied fluences. In order to estimate the total amorphization of the SiC crystal for different ions and fluences combination, an assessment model was proposed. For this purpose, 4 MeV carbon and silicon ions with multiple fluences were implanted in the [0001] axial direction of a 6H-SiC single crystal. The amorphization depth distributions were obtained by Elastic Backscattering Spectroscopy/channeling spectra analysis via Channeling SIMulation (CSIM) phenomenological computer code. As a result, relation of the total induced amorphization and implantation fluences for carbon and silicon ions were obtained. Based on these experimental results, a total amorphization assessment model for different ions (energy of 4 MeV) and fluences combination was established.